DRA2143Y

Silicon PNP epitaxial planar type

For digital circuits Complementary to DRC2143Y

Features

- \bullet High forward current transfer ratio h_{FE}
- \bullet Low collector-emitter saturation voltage $V_{CE(\text{sat})}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

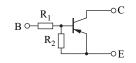
U <i>u</i>								
Parameter	Symbol	Rating	Unit					
Collector-base voltage (Emitter open)	V _{CBO}	-50	V					
Collector-emitter voltage (Base open)	V _{CEO}	-50	V					
Collector current	I _C	-100	mA					
Total power dissipation	P _T	200	mW					
Junction temperature	Tj	150	°C					
Storage temperature	T _{stg}	-55 to +150	°C					



- Code
- Mini3-G3-B
- Pin Name
 - 1: Base
 - 2: Emitter
 - 3: Collector

Marking Symbol: L7

Internal Connection



Resistance value	R ₁	4.7	kΩ
	R ₂	22	kΩ

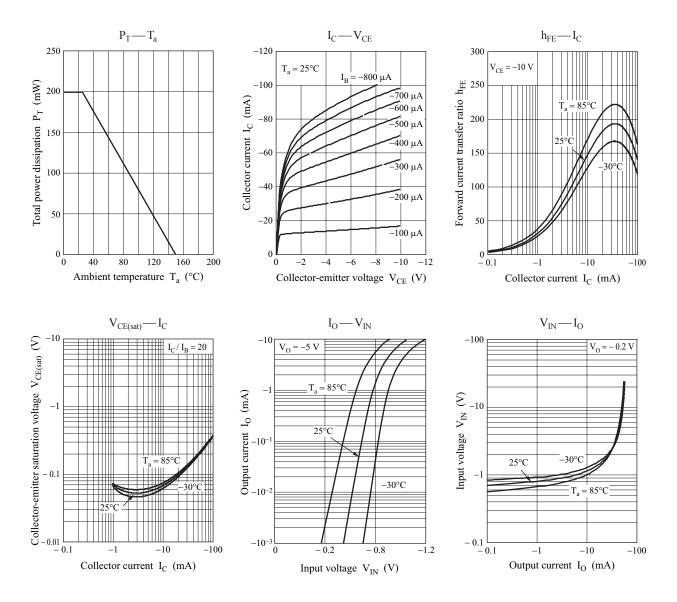
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{\rm CB} = -50$ V, $I_{\rm E} = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{\rm CE} = -50$ V, $I_{\rm B} = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{\rm EB} = -6$ V, $I_{\rm C} = 0$			- 0.4	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	60		200	
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.5 \text{ mA}$			-0.25	V
Input voltage (ON)	V _{I(on)}	$V_{\rm CE} = -0.2$ V, $I_{\rm C} = -5$ mA	-1.2			V
Input voltage (OFF)	V _{I(off)}	$V_{CE} = -5 \text{ V}, I_C = -100 \mu\text{A}$			- 0.5	V
Input resistance	R ₁		-30%	4.7	+30%	kΩ
Resistance ratio	R ₁ / R ₂		0.17	0.21	0.27	_

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

DRA2143Y

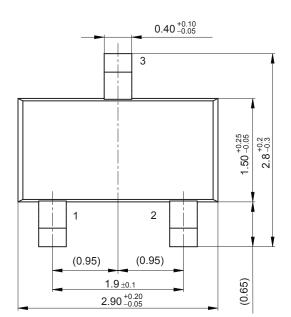
Panasonic

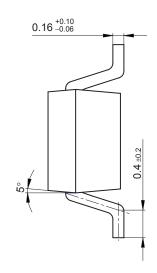


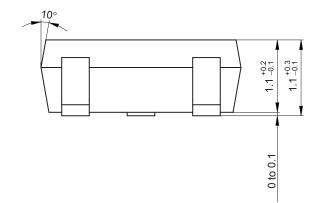
Panasonic

Mini3-G3-B

Unit: mm







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